

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
SEC.1100

In Re Application Of: **Young-man HWANG et al.**

Serial No.
NEW

Filing Date
MARCH 1, 2004

Examiner
TO BE ASSIGNED

Group Art Unit
TO BE ASSIGNED

Title: **PHASE-CHANGE MEMORY AND METHOD HAVING RESTORE FUNCTION**

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

OR

☐ the fee set forth in 37 CFR 1.17(p).

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Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
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Dated: MARCH 1, 2004

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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

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Applicant(s)

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A	6,545,907	04/08/2003	LOWREY et al.			
	B	2003/0002332	01/02/2003	LOWREY			
	C	6,487,113	11/26/2002	PARK et al.			
	D	6,075,719	06/13/2000	LOWREY et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	E	Y.N. Hwang et al., "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors"
	F	Manzur Gill et al., "Ovonic Unified Memory - A High-Performance Nonvolatile Memory Technology for Stand-Alone Memory and Embedded Applications," ISSCC 2002/Session 12/TD: Digital Directions/12.4, pages 158-159, and 445-446.

EXAMINER	DATE CONSIDERED
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INFORMATION DISCLOSURE CITATION*(Use several sheets if necessary)*

Docket Number (Optional)

SEC.1100

Application Number

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Applicant(s)

Young-man HWANG et al.

Filing Date

March 1, 2004

Group Art Unit

TO BE ASSIGNED***EXAMINER
INITIAL****OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)***G****Stefan Lai et al., "OUM - A 180 nm Nonvolatile Memory Cell Element Technology For Stand Alone and Embedded Applications," IEDM 01-803 - 806.****H****Y.N. Hwang et al., "Phase-Change Chalcogenide Nonvolatile RAM Completely Based on CMOS Technology"****I****Linda Geppert, "The New Indelible Memories," IEEE Spectrum, March 2003, pages 49-54.****J****Jon Maimon et al., "Chalcogenide-Based Non-Volatile Memory Technology," pages 5-2289 - 5-2294.****EXAMINER****DATE CONSIDERED*****EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.**